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# **Silicon Compatible Emerging Materials, Processes, and Technologies for Advanced CMOS and Post- CMOS Applications 11**

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**Editors:****H. Jagannathan****P. Timans****K. Kakushima****E. P. Gusev****Z. Karim****D. Misra****Y. Obeng****S. De Gendt****F. Roozeboom****Sponsoring Divisions:****Dielectric Science and Technology****Electronics and Photonics****Published by****The Electrochemical Society**65 South Main Street, Building D  
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